



POWER DISCRETES & MODULES

- ▶ Silicon Carbide (SiC)
- ▶ Diode and Rectifier Devices
- ▶ Voltage & Current Regulation Diodes
- ▶ Small Signal Diodes and Diode Arrays
- ▶ IGBT
- ▶ Power MOSFET
- ▶ Power Modules
- ▶ JFET
- ▶ BJT (BiPolar Junction Transistor)
 - BJT Modules (Power Integrated Circuit, PIC)
 - Darlington Transistors
 - Darlington Transistor Array
 - NPN PNP Complimentary Transistor
 - NPN Transistor
 - **PNP Transistor**
- ▶ Legacy Power Discretets & Modules

[Home](#) / [Power Discretets & Modules](#) / [BJT \(BiPolar Junction Transistor\)](#) / [PNP Transistor](#) / 2N5782 (#23862)

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Product Status

■ In Production

[Overview](#) [Resources](#) [Diagrams](#) [Ordering](#) [Support](#)

Package ESD Bag
Carrier:

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$			0.75	V
DC Current Gain	HFE	20		100	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter O	$V_{BR(CBO)}$			65	V
Collector Current (dc)	I_C			3.5	A
Collector-Emitter Voltage (Base Open)	V_{CEO}			50	V
Emitter-Base Voltage (Collector Open)	V_{EBO}			5.5	V
Power Dissipation	P_D			10	W

This part can be found in the following product categories:

- [Power Discretets & Modules](#) ▶ [BJT \(BiPolar Junction Transistor\)](#) ▶ [PNP Transistor](#)